PECJ100N06A

Description

PECJ N-channel Enhancement Mode Power MOSFET

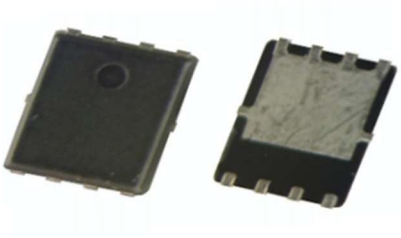
Features

- 60V, 55A
  $R_{DS(ON)}$ <10mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$ <14mΩ @ V_{GS} = 4.5V
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

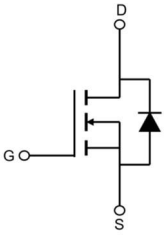
- Load Switch
- PWM Application
- Power management

100% UIS TESTED!
100% ΔVds TESTED!



PDFN5X6-8L

Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
60N04	PECJ100N06A	TAPING	PDFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	55	A
		T_C = 100℃	36	A
I_{DM}	Pulsed Drain Current note1		220	A
E_{AS}	Single Pulsed Avalanche Energy note2		81	mJ
P_D	Power Dissipation	T_C = 25℃	53	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.4	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS} = 0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.7	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=20A	-	7.5	10	mΩ
		V_{GS}=4.5V, I_D=15A	-	10	14	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	4605	-	pF
C_{oss}	Output Capacitance		-	215	-	pF
C_{rss}	Reverse Transfer Capacitance		-	191	-	pF
Q_g	Total Gate Charge	V_{DS}=30V, I_D=20A, V_{GS}=10V	-	77	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	23	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=30V, I_D=30A, R_G=1.8Ω, V_{GS}=10V	-	7.1	-	ns
t_r	Turn-on Rise Time		-	5.3	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	27.2	-	ns
t_f	Turn-off Fall Time		-	6.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	55	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	220	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=30A, dI/dt=100A/μs	-	29	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	45	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω,I_{AS}=18A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

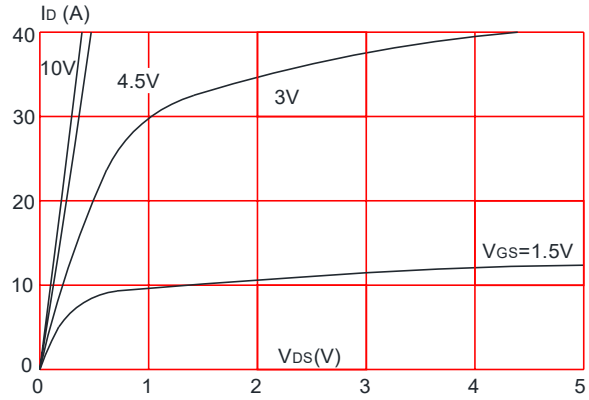


Figure 2: Typical Transfer Characteristics

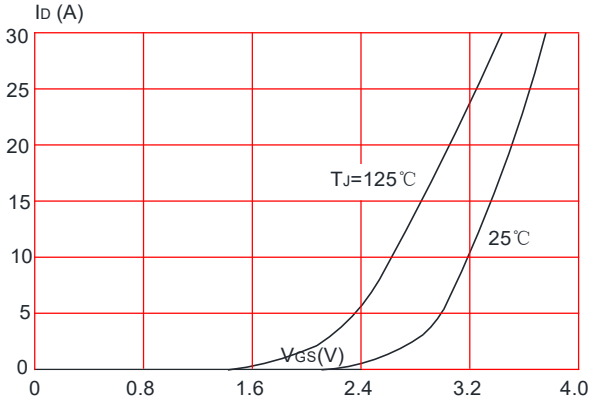


Figure 3: On-resistance vs. Drain Current

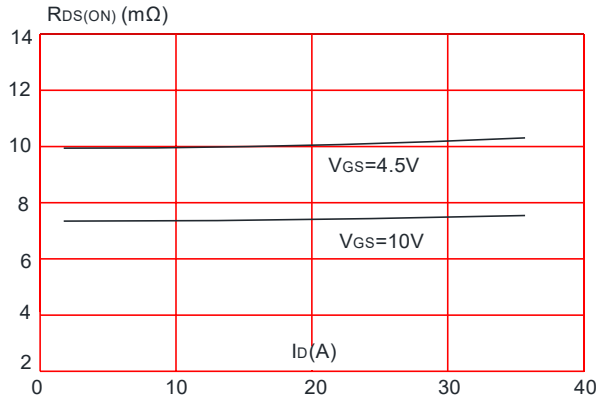


Figure 4: Body Diode Characteristics

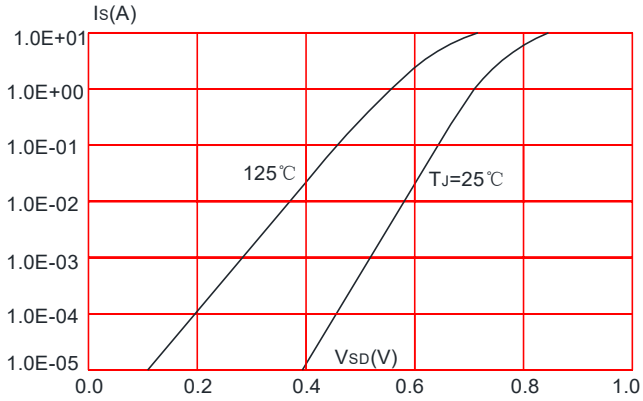


Figure 5: Gate Charge Characteristics

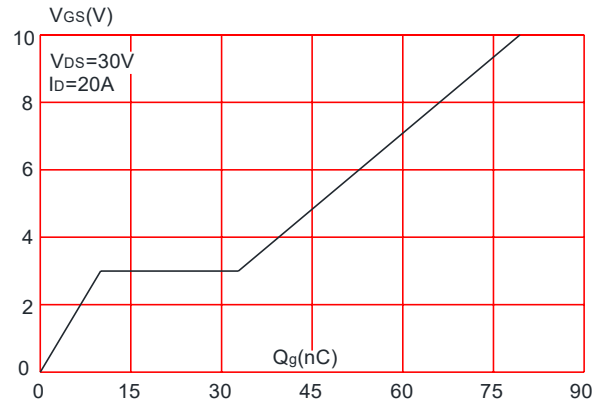


Figure 6: Capacitance Characteristics

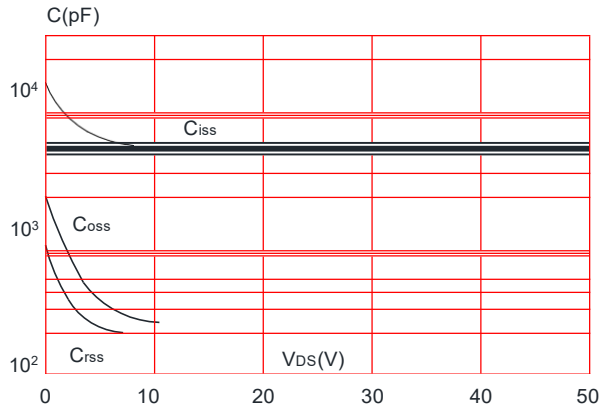


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

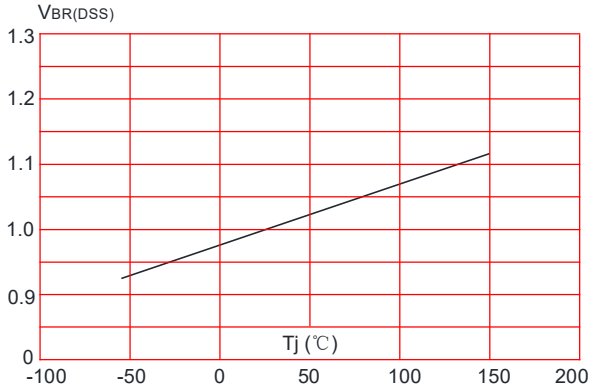


Figure 8: Normalized on Resistance vs. Junction Temperature

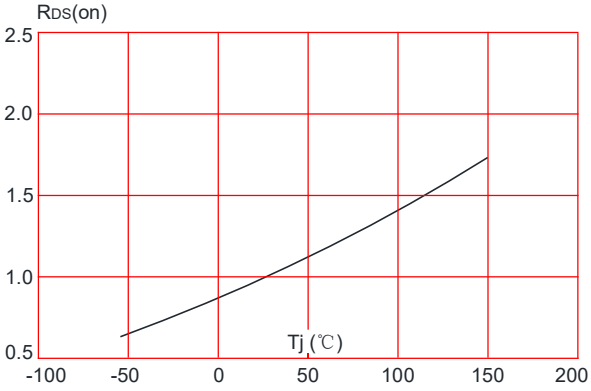


Figure 9: Maximum Safe Operating Area

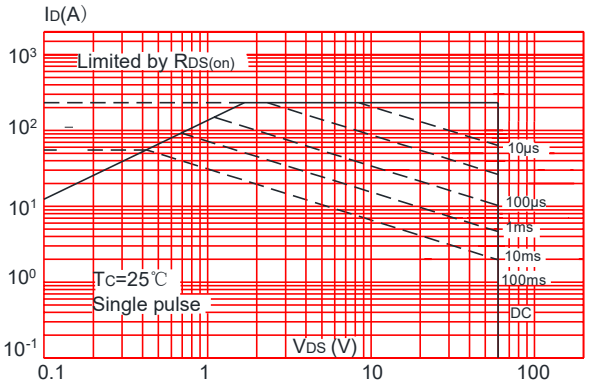


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

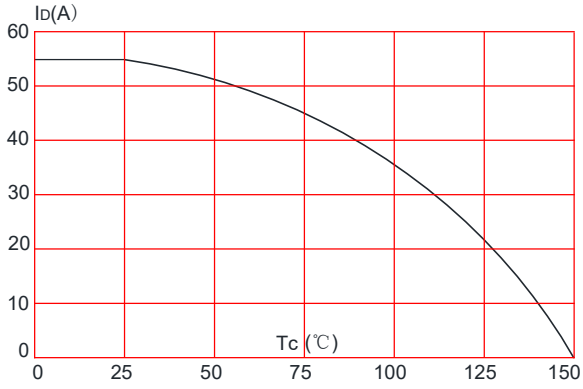
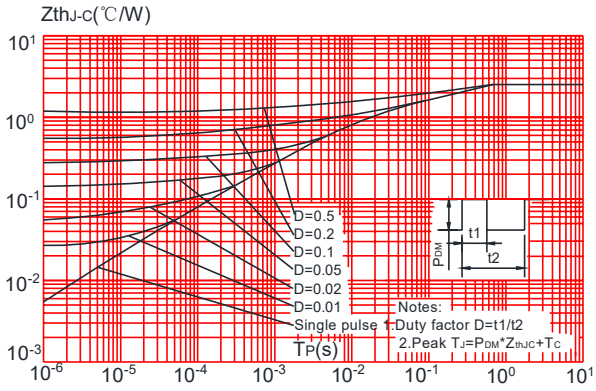


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

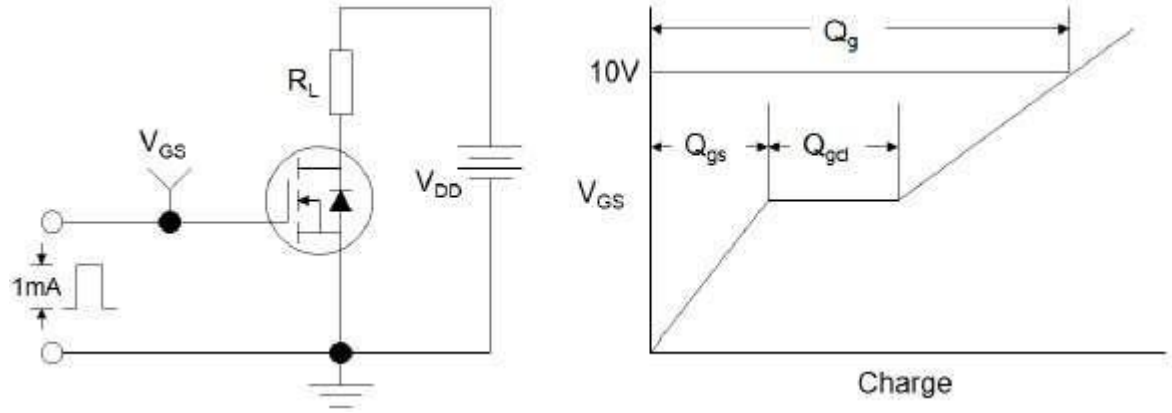


Figure1:Gate Charge Test Circuit & Waveform

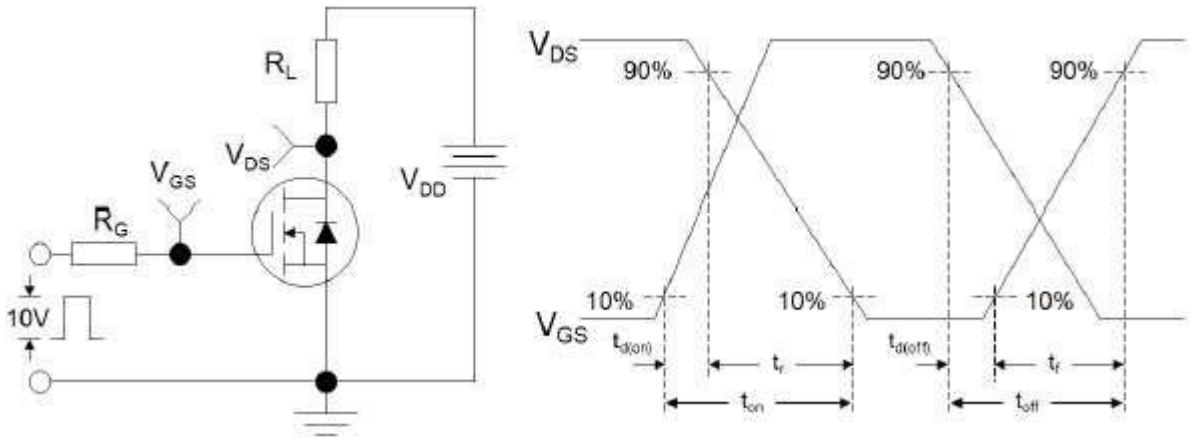


Figure 2: Resistive Switching Test Circuit & Waveforms

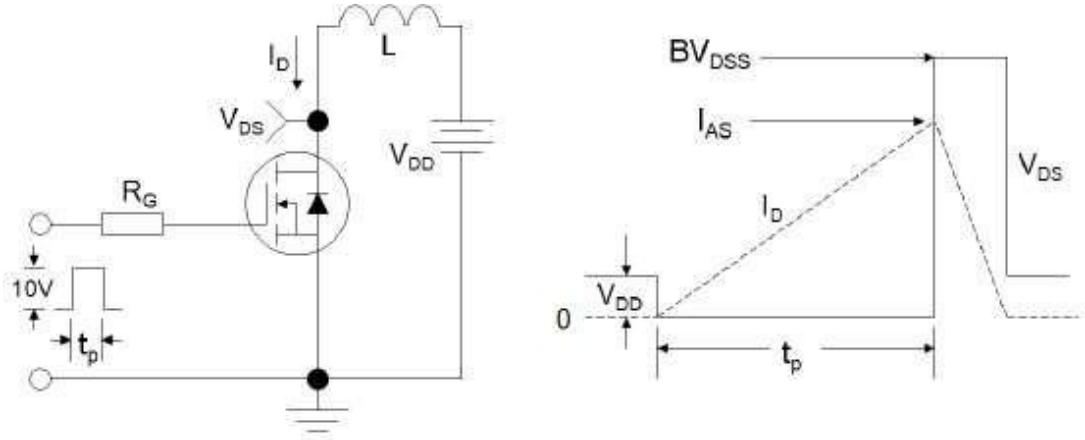
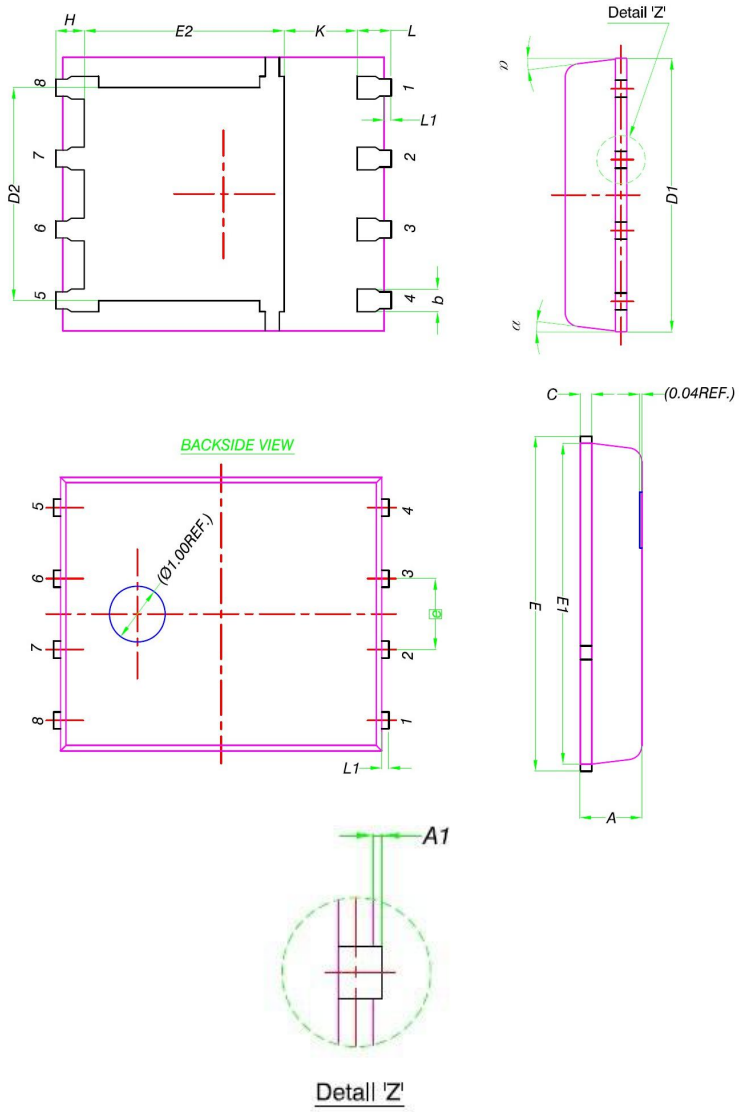


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data- PDFN5X6-8L



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°